

HORIZONTAL DEFLECTION POWER TRANSISTORS

...specifically designed for use in larg screen color deflection circuits.

FEATURES:

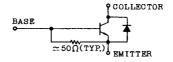
- * High Voltage: V_{CBO}=1500V

 * Low Saturation Voltage: V_{CE(sat)}=5.0V(Max.) @ I_C = 5.0 A

 * High Speed: t_t =1.0 us(Max.) @ I_{CP} =5.0 A, I_{B1} =1.0A

 * Built-in Damper Type

- * Glass Passivated Collector-Base Junction

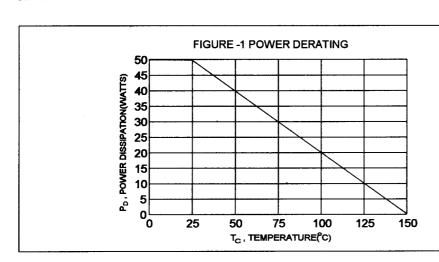


MAXIMUM RATINGS

Charácteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CBO}	1500	V
Collector-Emitter Voltage	V _{CEO}	600	V
Emitter-Base Voltage	V _{EBO}	5.0	V
Collector Current-Continuous	l _c	6.0	А
Base Current	I _B	3.0	Α
Total Power Dissipation @T _C =25°C Derate above 25°C	P _D	50 0.4	W/°C
Operating and Storage Junction Temperature Range	T _J ,T _{STG}	- 65 to +150	°C

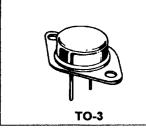
THERMAL CHARACTERISTICS

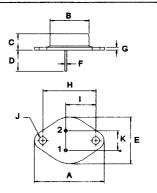
Characteristic	Symbol	Max	Unit
Thermal Resistance Junction to Case	R⊕jc	2.5	°C/W



NPN 2SD871

6 AMPERE **POWER TRANSISTORS 1500 VOLTS** 50 WATTS





PIN 1.BASE 2.EMITTER COLLECTOR(CASE)

DIM	MILLIMETERS			
Dilai	MIN	MAX		
Α	38.75	39.96		
В	19.28	22.23		
С	7.96	9.28		
D	11.18	12.19		
E	25.20	26,67		
F	0.92	1.09		
G	1.38	1.62		
Н	29.90	30.40		
ı	16.64	17.30		
J	3.88	4.36		
K	10.67	11.18		

ELECTRICAL CHARACTERISTICS ($T_c = 25^{\circ}C$ unless otherwise noted)

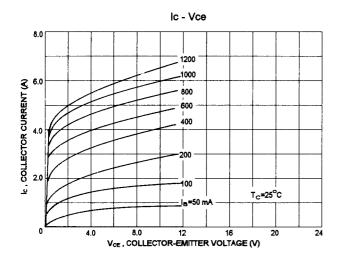
Max	Unit
10	uA
	V
5.0	٧
1.5	٧
2.0	V
	2.0
	5.0

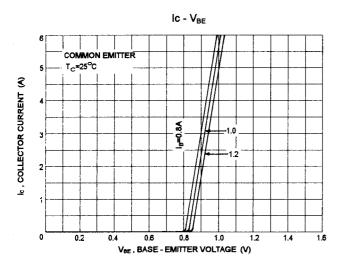
Current Gain - Bandwidth Product (I _C = 0.1 A, V _{CE} = 10 V, f = 1.0 MHz)	f _T	3.0(Typ)	MHz
Collector Output Capacitance (V _{CB} = 10 V, I _E = 0, f = 1.0 MHz)	Сор	170(Typ)	pF

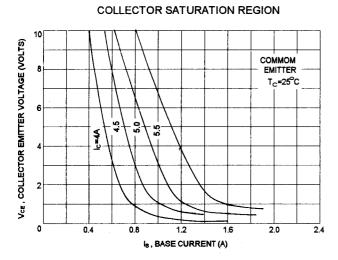
SWITCHING CHARATERISTICS

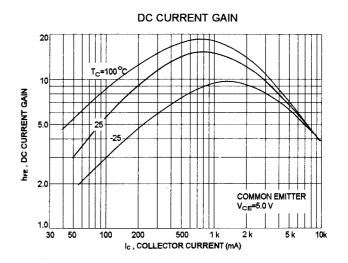
SWITCHING CHARATERISTICS					
Fall Time	I _C = 5.0A ,I _{B1 (end)} =1.0A	tr		1.0	us

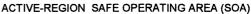
⁽¹⁾ Pulse Test: Pulse width $\, \leqq \,$ 300 μs , Duty Cycle $\, \leqq \,$ 2.0%

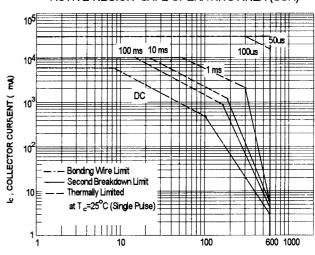












 V_{CE} , COLLECTOR EMITTER VOLTAGE (VOLTS)

There are two limitation on the power handling ability of a transistor:average junction temperature and second breakdown safe operating area curves indicate $I_{\text{\tiny C}}\text{-}V_{\text{\tiny CE}}$ limits of the transistor that must be observed for reliable operation i.e., the transistor must not be subjected to greater dissipation than curves indicate.

The data of SOA curve is base on $T_{J(PK)}$ =150 °C; T_C is variable depending on conditions. second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(PK)}$ ≤150°C,At high case temperatures, thermal limitation will reduce the power that can be handled to values less than the limitations imposed by second breakdown.



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